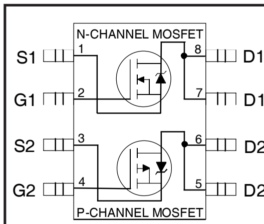
International
IOR Rectifier

PD - 96110A

IRF7343QPBF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dual N and P Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- 150°C Operating Temperature
- Lead-Free



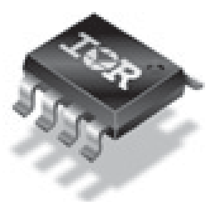
Top View

	N-Ch	P-Ch
V_{DSS}	55V	-55V
$R_{DS(on)}$	0.050Ω	0.105Ω

Description

These HEXFET® Power MOSFET's in a Dual SO-8 package utilize the lastest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of these HEXFET Power MOSFET's are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in a wide variety of applications.

The efficient SO-8 package provides enhanced thermal characteristics and dual MOSFET die capability making it ideal in a variety of power applications. This dual, surface mount SO-8 can dramatically reduce board space and is also available in Tape & Reel.


SO-8

Absolute Maximum Ratings

	Parameter	Max.		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	55	-55	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	4.7	-3.4	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	3.8	-2.7	
I_{DM}	Pulsed Drain Current ①	38	-27	
P_D @T_A = 25°C	Maximum Power Dissipation ⑤	2.0		W
P_D @T_A = 70°C	Maximum Power Dissipation ⑤	1.3		W
E_{AS}	Single Pulse Avalanche Energy③	72	114	mJ
I_{AR}	Avalanche Current	4.7	-3.4	A
E_{AR}	Repetitive Avalanche Energy	0.20		mJ
V_{GS}	Gate-to-Source Voltage	± 20		V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	-5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150		°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ⑤	–––	62.5	°C/W

08/09/10

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter		Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	N-Ch	55	—	—	V	V_{GS} = 0V, I_D = 250μA
		P-Ch	-55	—	—		V_{GS} = 0V, I_D = -250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	N-Ch	—	0.059	—	V/°C	Reference to 25°C, I_D = 1mA
		P-Ch	—	0.054	—		Reference to 25°C, I_D = -1mA
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	N-Ch	—	0.043	0.050	Ω	V_{GS} = 10V, I_D = 4.7A ④
			—	0.056	0.065		V_{GS} = 4.5V, I_D = 3.8A ④
		P-Ch	—	0.095	0.105		V_{GS} = -10V, I_D = -3.4A ④
			—	0.150	0.170		V_{GS} = -4.5V, I_D = -2.7A ④
$V_{GS(th)}$	Gate Threshold Voltage	N-Ch	1.0	—	—	V	V_{DS} = V_{GS}, I_D = 250μA
		P-Ch	-1.0	—	—		V_{DS} = V_{GS}, I_D = -250μA
g_{fs}	Forward Transconductance	N-Ch	7.9	—	—	S	V_{DS} = 10V, I_D = 4.5A ④
		P-Ch	3.3	—	—		V_{DS} = -10V, I_D = -3.1A ④
I_{DSS}	Drain-to-Source Leakage Current	N-Ch	—	—	2.0	μA	V_{DS} = 55V, V_{GS} = 0V
		P-Ch	—	—	-2.0		V_{DS} = -55V, V_{GS} = 0V
		N-Ch	—	—	25		V_{DS} = 55V, V_{GS} = 0V, T_J = 55°C
		P-Ch	—	—	-25		V_{DS} = -55V, V_{GS} = 0V, T_J = 55°C
I_{GSS}	Gate-to-Source Forward Leakage	N-P	—	—	±100	nA	V_{GS} = ±20V
Q_g	Total Gate Charge	N-Ch	—	24	36	nC	N-Channel I_D = 4.5A, V_{DS} = 44V, V_{GS} = 10V ④ P-Channel I_D = -3.1A, V_{DS} = -44V, V_{GS} = -10V
		P-Ch	—	26	38		
Q_{gs}	Gate-to-Source Charge	N-Ch	—	2.3	3.4		
		P-Ch	—	3.0	4.5		
Q_{gd}	Gate-to-Drain ("Miller") Charge	N-Ch	—	7.0	10		
		P-Ch	—	8.4	13		
$t_{d(on)}$	Turn-On Delay Time	N-Ch	—	8.3	12	ns	N-Channel V_{DD} = 28V, I_D = 1.0A, R_G = 6.0Ω, R_D = 28Ω ④ P-Channel V_{DD} = -28V, I_D = -1.0A, R_G = 6.0Ω, R_D = 28Ω
		P-Ch	—	14	22		
t_r	Rise Time	N-Ch	—	3.2	4.8		
		P-Ch	—	10	15		
$t_{d(off)}$	Turn-Off Delay Time	N-Ch	—	32	48		
		P-Ch	—	43	64		
t_f	Fall Time	N-Ch	—	13	20		
		P-Ch	—	22	32		
C_{iss}	Input Capacitance	N-Ch	—	740	—	pF	N-Channel V_{GS} = 0V, V_{DS} = 25V, ƒ = 1.0MHz P-Channel V_{GS} = 0V, V_{DS} = -25V, ƒ = 1.0MHz
		P-Ch	—	690	—		
C_{oss}	Output Capacitance	N-Ch	—	190	—		
		P-Ch	—	210	—		
C_{rss}	Reverse Transfer Capacitance	N-Ch	—	71	—		
		P-Ch	—	86	—		

Source-Drain Ratings and Characteristics

	Parameter		Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	N-Ch	—	—	2.0	A	
		P-Ch	—	—	-2.0		
I_{SM}	Pulsed Source Current (Body Diode) ①	N-Ch	—	—	38		
		P-Ch	—	—	-27		
V_{SD}	Diode Forward Voltage	N-Ch	—	0.70	1.2	V	T_J = 25°C, I_S = 2.0A, V_{GS} = 0V ③
		P-Ch	—	-0.80	-1.2		T_J = 25°C, I_S = -2.0A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	N-Ch	—	60	90	ns	N-Channel T_J = 25°C, I_F =2.0A, di/dt = 100A/μs P-Channel T_J = 25°C, I_F = -2.0A, di/dt = 100A/μs ④
		P-Ch	—	54	80		
Q_{rr}	Reverse Recovery Charge	N-Ch	—	120	170	nC	
		P-Ch	—	85	130		

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 22)

② N-Channel $I_{SD} \le$ 4.7A, di/dt $\le$ 220A/μs, $V_{DD} \le V_{(BR)DSS}$, $T_J \le$ 150°C
P-Channel $I_{SD} \le$ -3.4A, di/dt $\le$ -150A/μs, $V_{DD} \le V_{(BR)DSS}$, $T_J \le$ 150°C

③ N-Channel Starting T_J = 25°C, L = 6.5mH R_G = 25Ω, I_{AS} = 4.7A.
P-Channel Starting T_J = 25°C, L = 20mH R_G = 25Ω, I_{AS} = -3.4A.

④ Pulse width $\le$ 300μs; duty cycle $\le$ 2%.

⑤ Surface mounted on FR-4 board, t $\le$ 10sec.

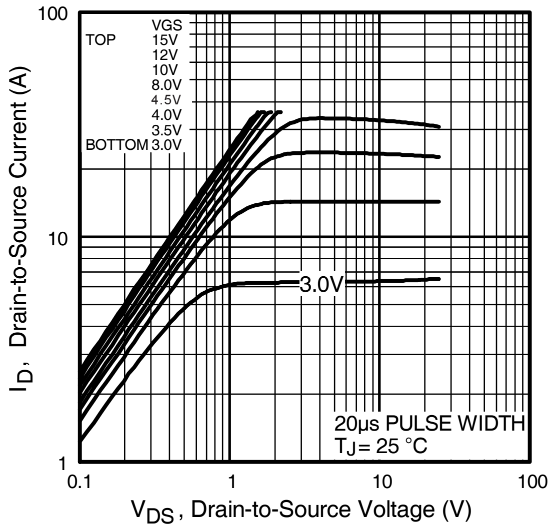


Fig 1. Typical Output Characteristics

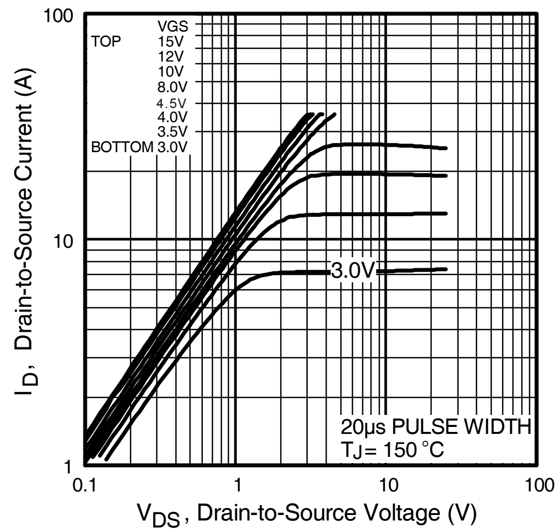


Fig 2. Typical Output Characteristics

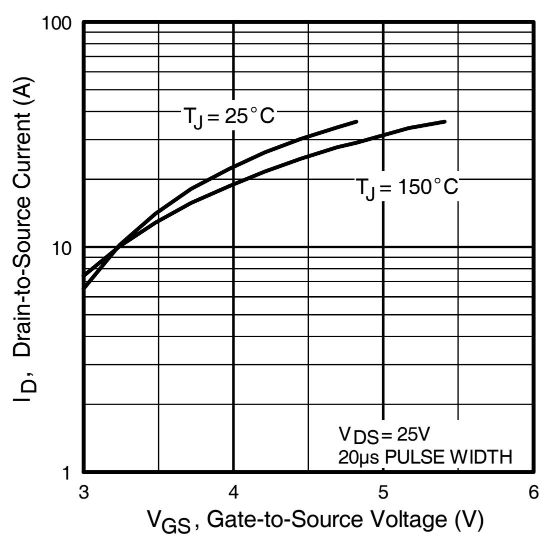


Fig 3. Typical Transfer Characteristics

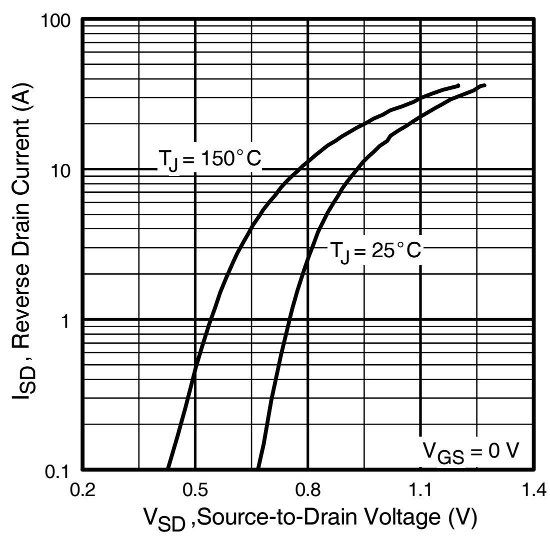


Fig 4. Typical Source-Drain Diode Forward Voltage

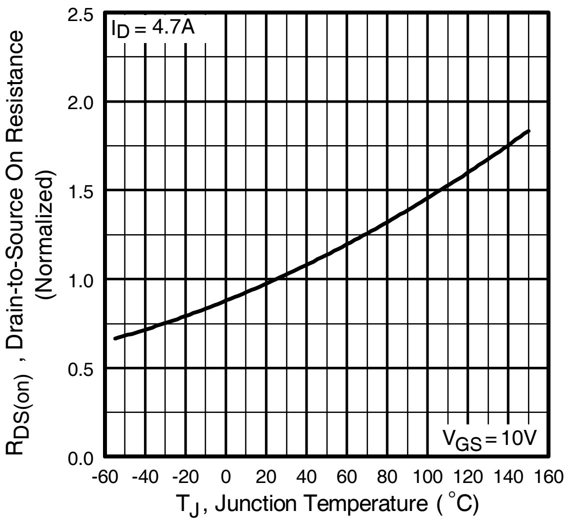


Fig 5. Normalized On-Resistance Vs. Temperature

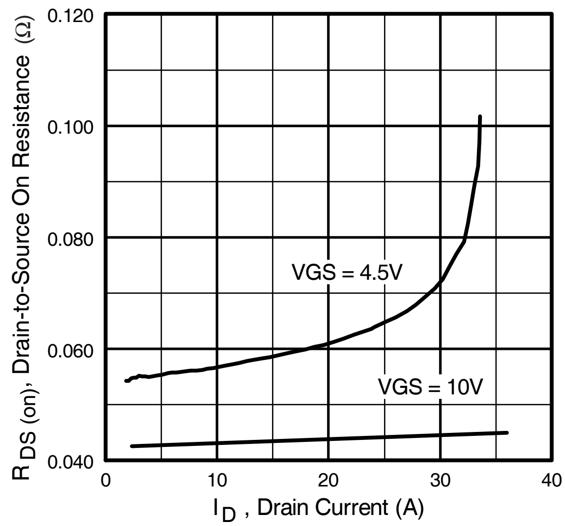


Fig 6. Typical On-Resistance Vs. Drain Current

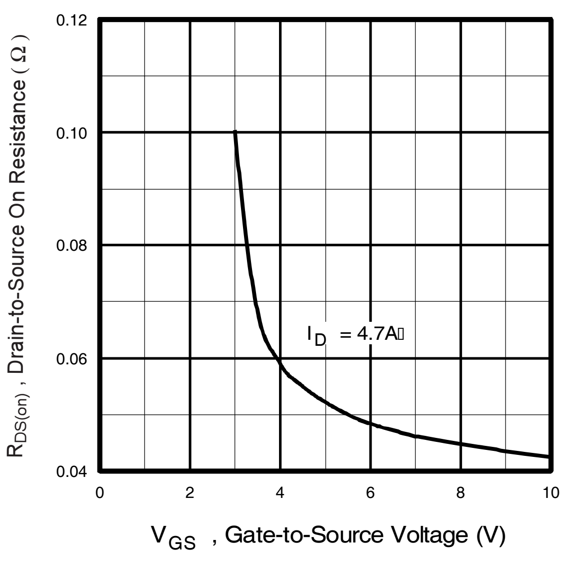


Fig 7. Typical On-Resistance Vs. Gate Voltage

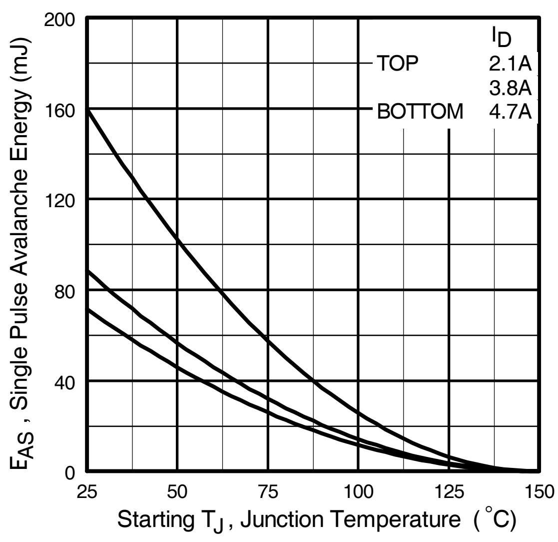


Fig 8. Maximum Avalanche Energy Vs. Drain Current

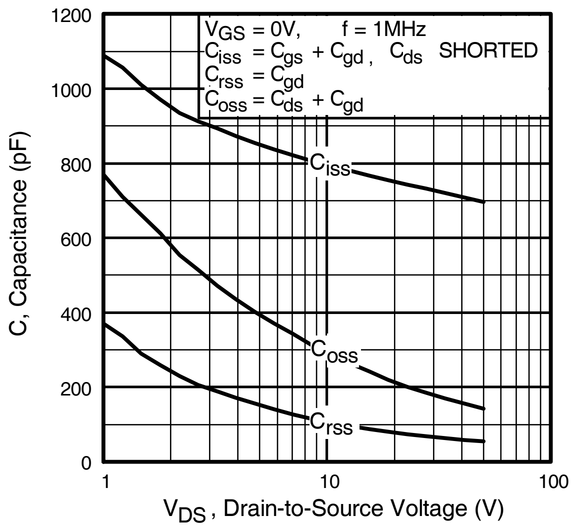


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

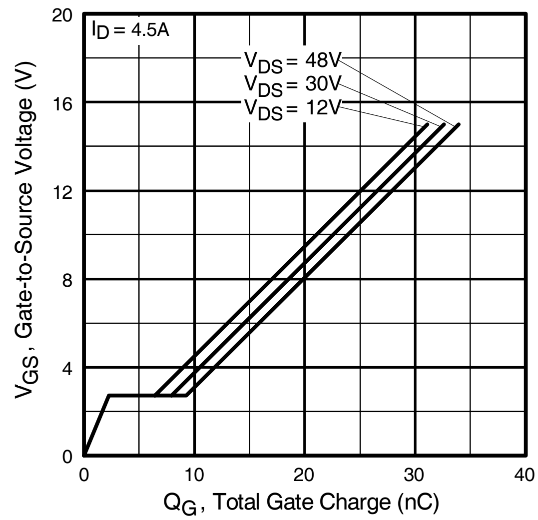


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

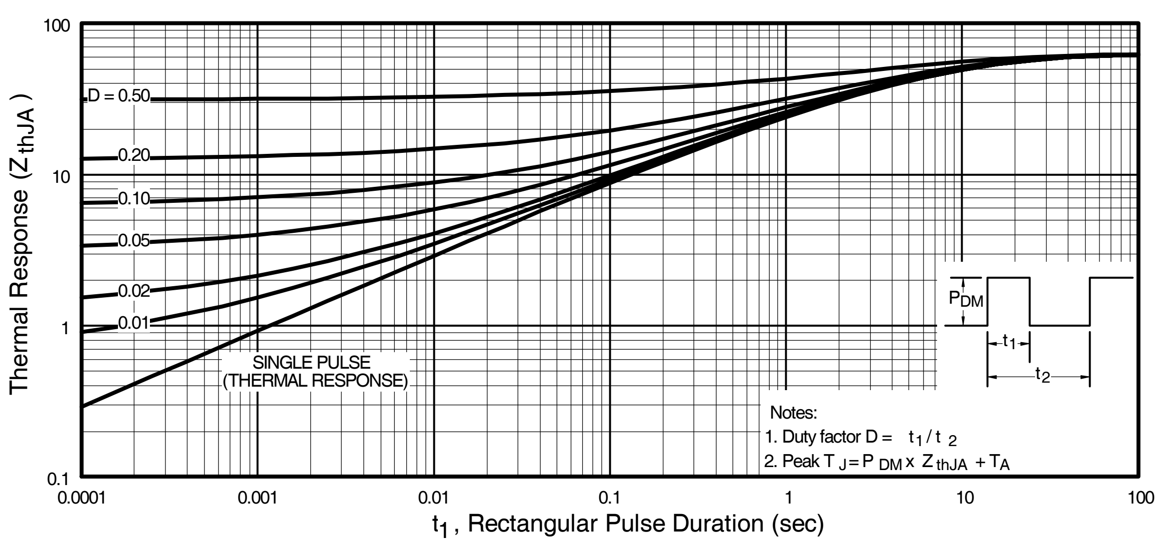


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

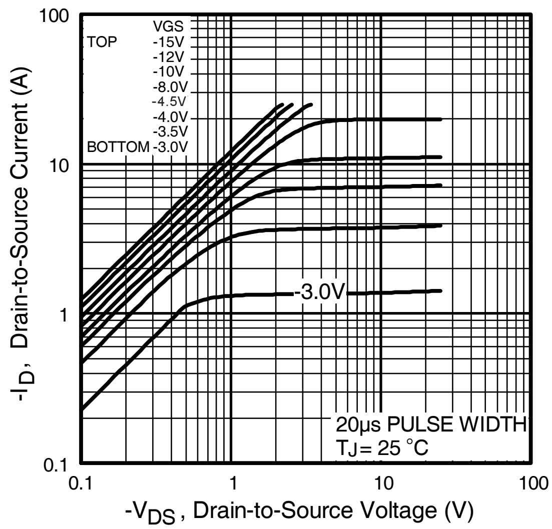


Fig 12. Typical Output Characteristics

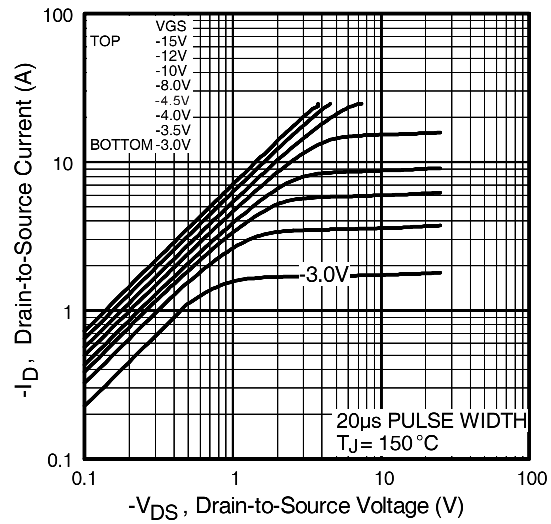


Fig 13. Typical Output Characteristics

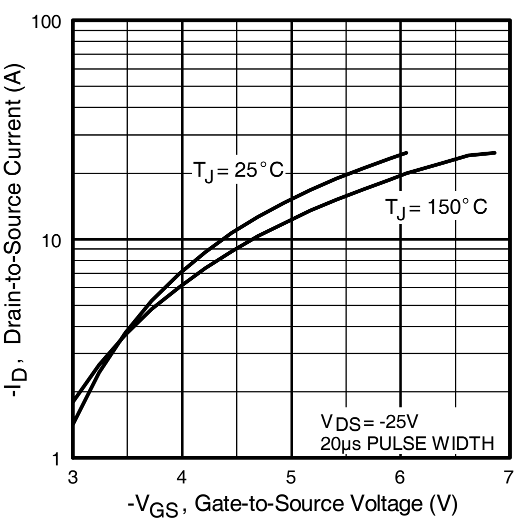


Fig 14. Typical Transfer Characteristics

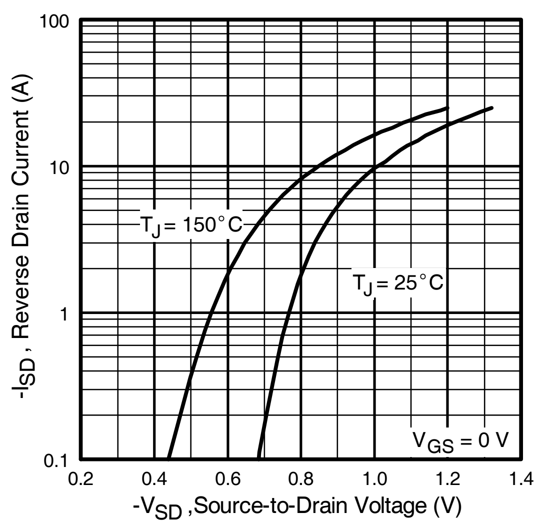


Fig 15. Typical Source-Drain Diode Forward Voltage

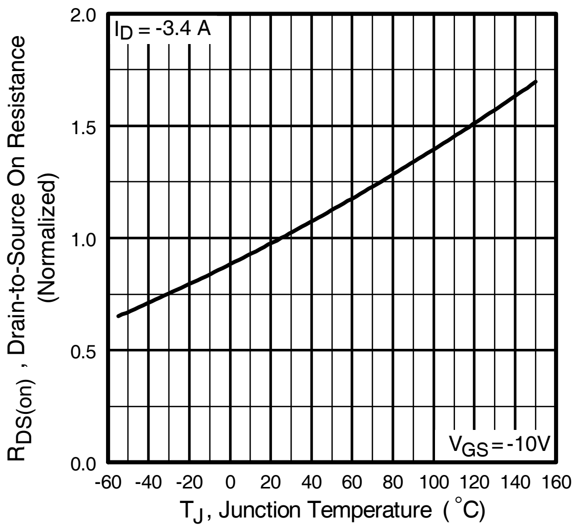


Fig 16. Normalized On-Resistance Vs. Temperature

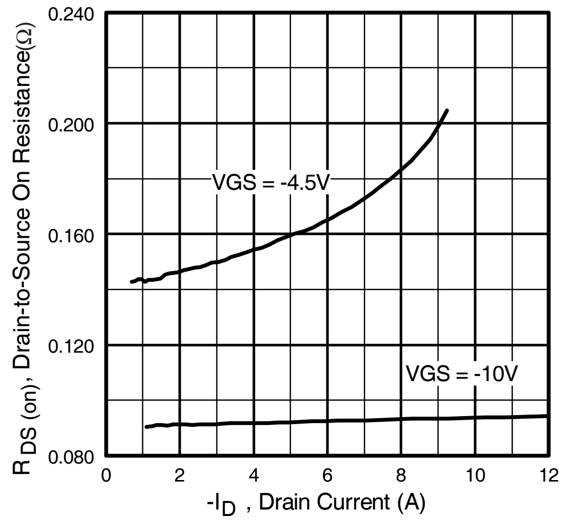


Fig 17. Typical On-Resistance Vs. Drain Current

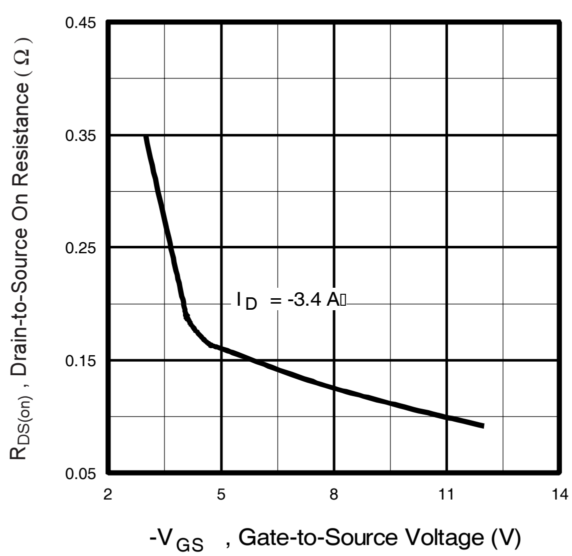


Fig 18. Typical On-Resistance Vs. Gate Voltage

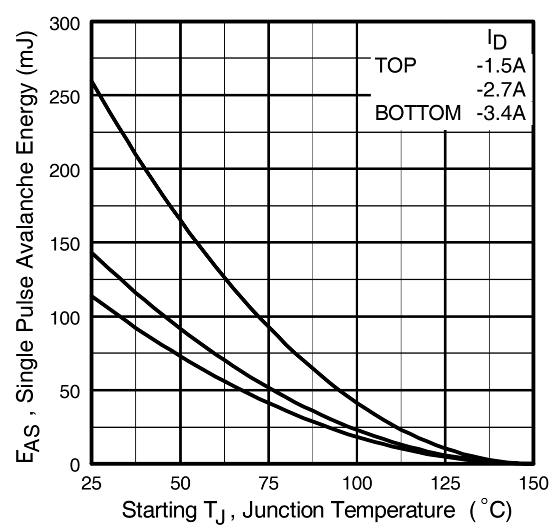


Fig 19. Maximum Avalanche Energy Vs. Drain Current

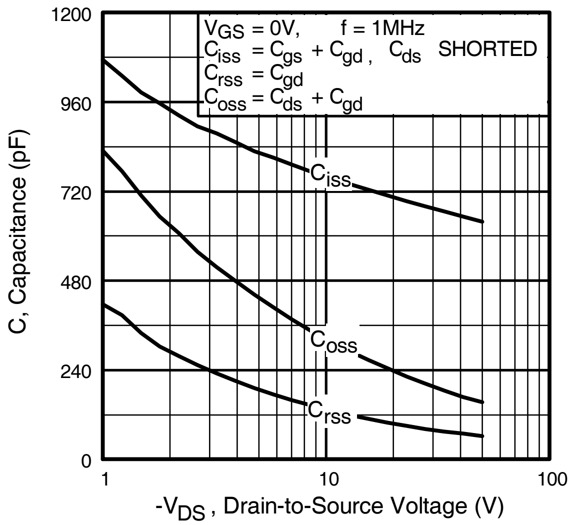


Fig 20. Typical Capacitance Vs. Drain-to-Source Voltage

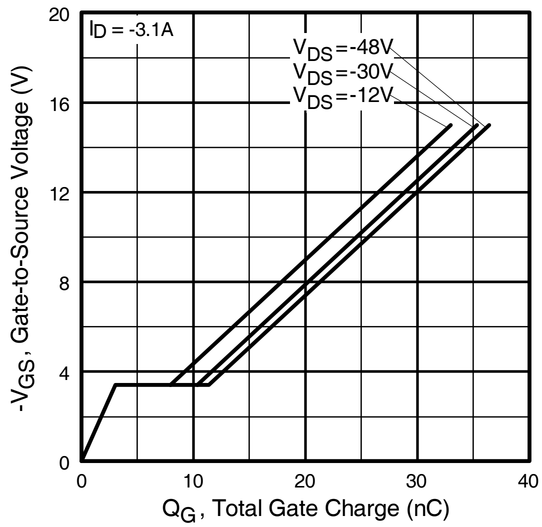


Fig 21. Typical Gate Charge Vs. Gate-to-Source Voltage

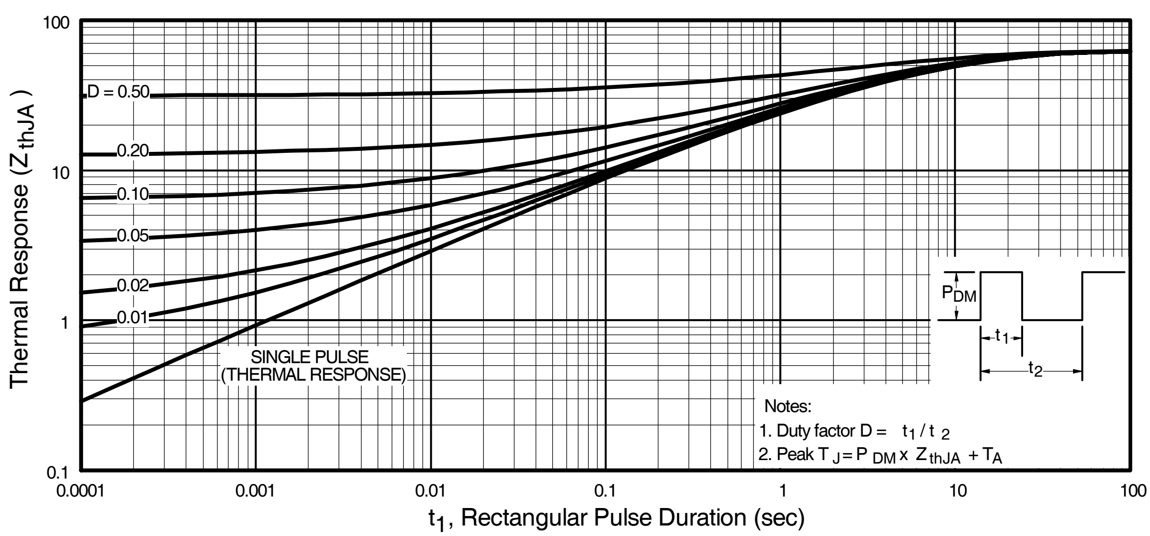
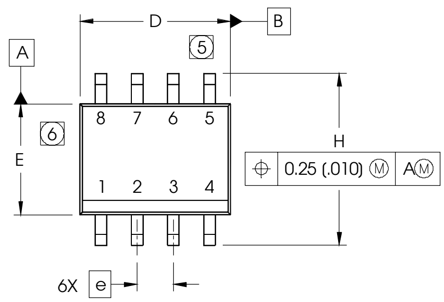


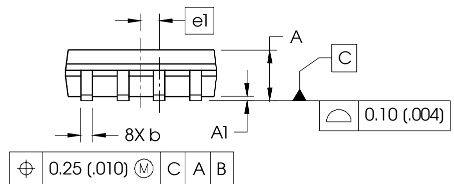
Fig 22. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

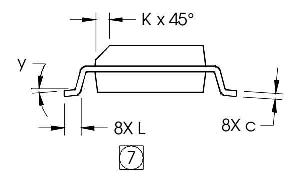
SO-8 Package Outline

Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

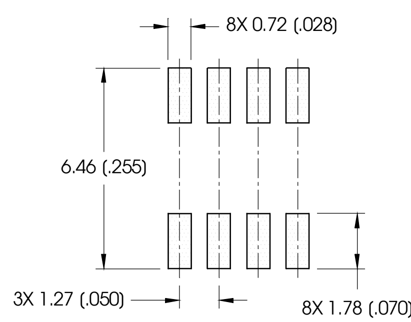




NOTES:

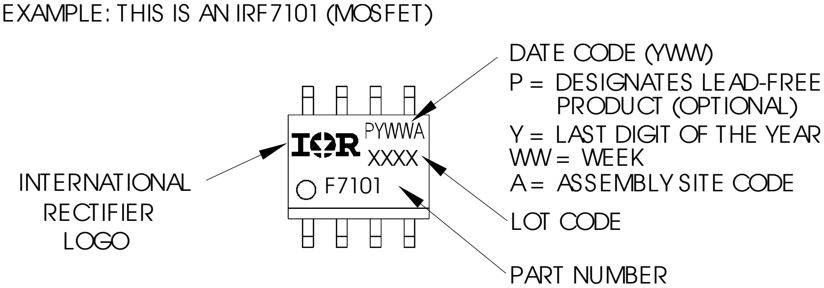
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



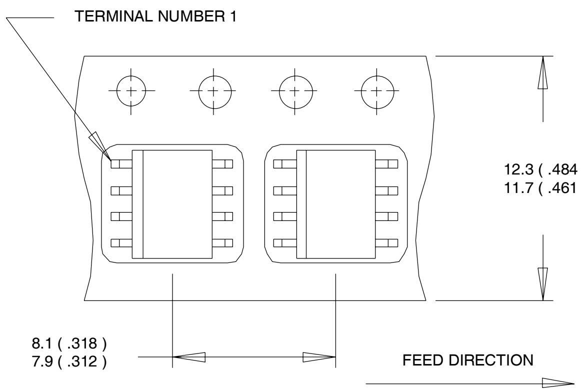
Notes:

1. For an Automotive Qualified version of this part please see http://www.irf.com/product-info/auto/

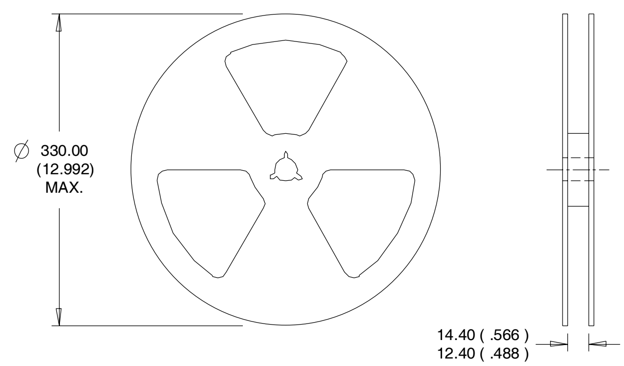
2. For the most current drawing please refer to IR website at http://www.irf.com/package/

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

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